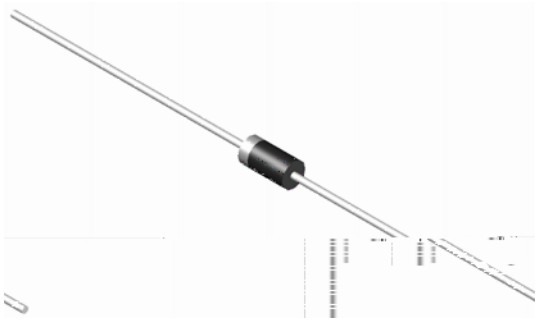
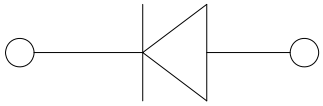
RoHS
COMPLIANT



Ultrafast reverse recovery time
Low leakage current
Low switching losses, high efficiency
High forward surge capability
Glass passivated chip junction
Solder dip 275 °C max. 7 s, per JESD 22-B106

For use in high frequency rectification and freewheeling application in switching mode converters and inverters for consumer, computer and telecommunication.



: DO-204AL(DO-41)
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
: Tin plated leads, solderable per J-STD-002 and JESD22-B102
Color band denotes the cathode end

■ (Ta=25 Unless otherwise specified

Device marking code			MUR120	MUR140	MUR160
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	V	200	400	600
Maximum RMS Voltage	V_{RMS}	V	140	280	420
Maximum DC blocking Voltage	V_{DC}	V	200	400	600
Average Forward Current @60Hz sine wave, Resistance load, Ta =75	$I_{F(AV)}$	A	1.0		
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave,1 cycle, Tj=25	I_{FSM}	A	35		
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, Tj=25			70		
Current squared time @1ms t 8.3ms Tj=25 Rating of per diode	I^2t	A^2s	5		
Typical junction capacitance @Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	Cj	pF	17	16	
Storage Temperature	T_{stg}		-55 ~ +150		
Junction Temperature	T_j		-55 ~ +150		

T_a=25 Unless otherwise specified

Maximum instantaneous forward voltage drop per diode	V_F	V	I_{FM}=1.0A	0.875	1.25	
Maximum DC reverse current at rated DC blocking voltage per diode	I_R	A	T_j=25	2.5		
			T_j=125	100		
Maximum reverse recovery time	t_{rr}	ns	I_F=0.5A,I_R=1.0A, I_{rr}=0.25A	25	50	

◆

Reverse Recovery Time	T_{RR}	ns	Tj=25	I_F=1A di/dt=-50A/us V_{RM}=30V	-	26	-
			Tj=25	I_F=1A di/dt=-200A/us V_{RM}=100V	-	21	-
			Tj=125		-	23	-
Peak recovery current	I_{RRM}	A	Tj=25		-	2.6	-
			Tj=125		-	3.9	-
Reverse recovery charge	Qrr	nC	Tj=25		-	26.8	-
			Tj=125		-	44.9	-
Non-repetitive avalanche energy	E_{AS}	mJ	Tj=25	I_R=1.6 A L=15 mH	19.2	-	-

◆

Reverse Recovery Time	T_{RR}	ns	Tj=25	I_F=1A di/dt=-50A/us V_{RM}=30V	-	46	-
			Tj=25	I_F=1A di/dt=-200A/us V_{RM}=400V	-	36	-
			Tj=125		-	56	-
Peak recovery current	I_{RRM}	A	Tj=25		-	3.6	-
			Tj=125		-	5.2	-
Reverse recovery charge	Qrr	nC	Tj=25		-	63.5	-
			Tj=125		-	144.5	-
Non-repetitive avalanche energy	E_{AS}	mJ	Tj=25	I_R=1.3A L=15 mH	12.7	-	-

T_a=25 Unless otherwise specified

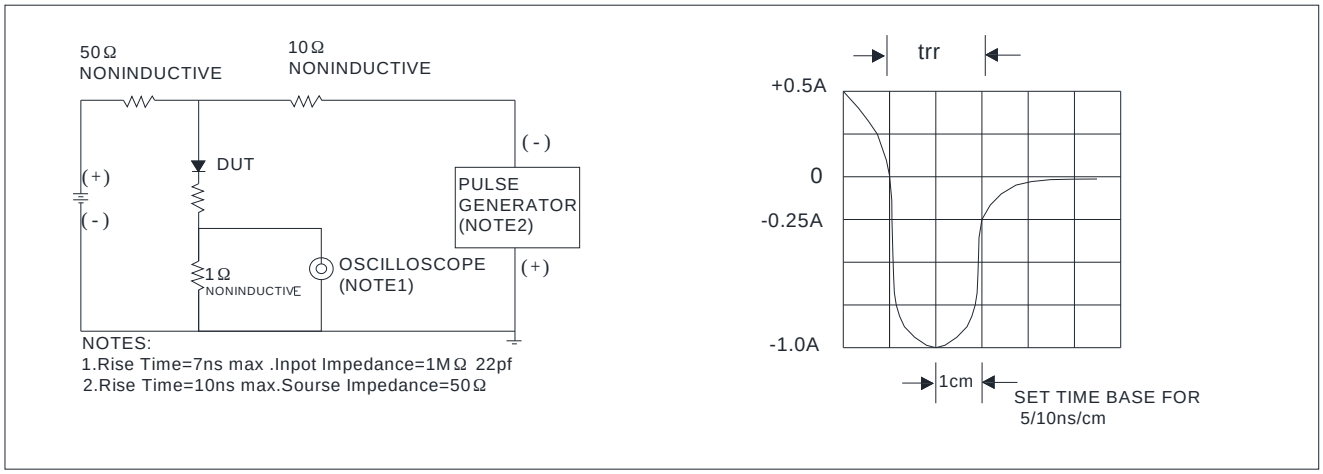
Typical Thermal Resistance	R_{J-A}	/W	60		

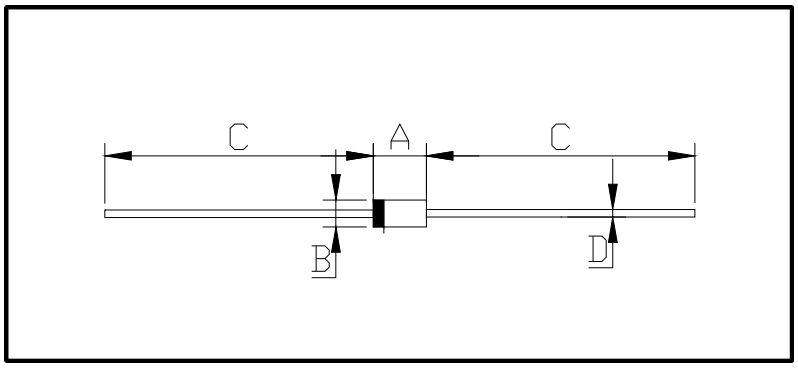
(Example)

MUR120~MUR160	D1	Approximate 0.30	5000	5000	50000	Tape
MUR120~MUR160	C1	Approximate 0.30	1000	1000	50000	Bulk

(Typical)

TJ=25





Dim	Min	Max
A	4.22	5.21
B	2.03	2.72
C	25.4	/
D	0.69	0.86

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and